

MOSFETs Silicon P-Channel MOS (U-MOSVI)

TPCF8107

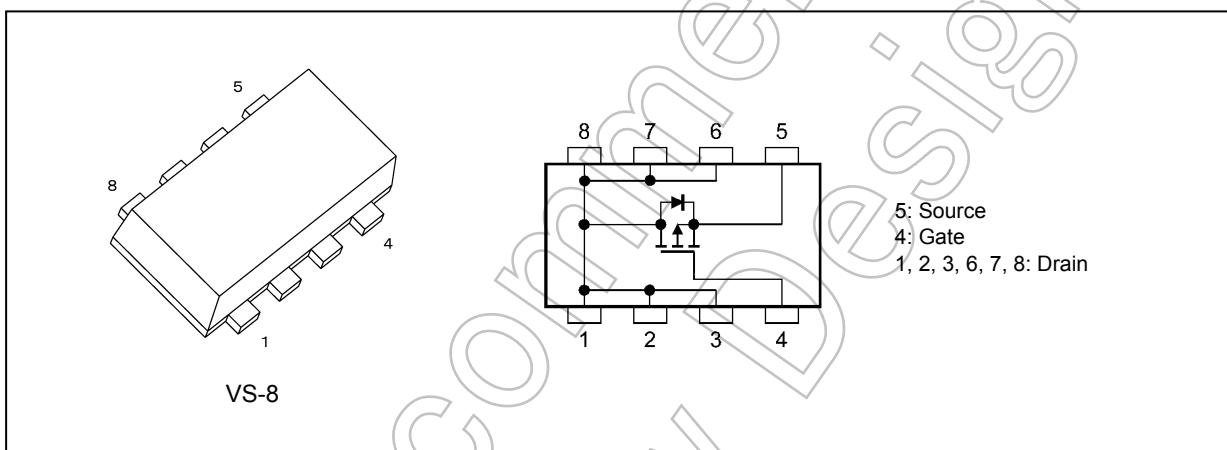
1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches
- Notebook PCs

2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 22 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = -10 \mu\text{A}$ (max) ($V_{DS} = -30 \text{ V}$)
- (4) Enhancement mode: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10 \text{ V}$, $I_D = -0.1 \text{ mA}$)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-30	V
Gate-source voltage	V_{GSS}	-25/+20	
Drain current (DC)	I_D	-6	A
Drain current (pulsed)	I_{DP}	-24	
Power dissipation ($t = 5 \text{ s}$)	P_D	2.5	W
Power dissipation ($t = 5 \text{ s}$)	P_D	0.7	W
Single-pulse avalanche energy	E_{AS}	23.4	mJ
Avalanche current	I_{AR}	-6	A
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Start of commercial production

2010-03

5. Thermal Characteristics

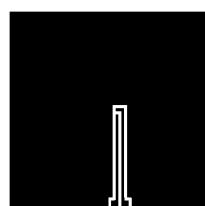
Characteristics		Symbol	Max	Unit
Channel-to-ambient thermal resistance ($t = 5$ s)	(Note 2)	$R_{th(ch-a)}$	50.0	°C/W
Channel-to-ambient thermal resistance ($t = 5$ s)	(Note 3)	$R_{th(ch-a)}$	178.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C.

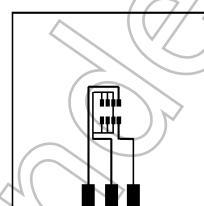
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: $V_{DD} = -24$ V, $T_{ch} = 25$ °C (initial), $L = 0.5$ mH, $R_G = 25$ Ω, $I_{AR} = -6$ A



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$	—	—	± 0.1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$	—	—	-10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -10\text{ mA}$, $V_{GS} = 0\text{ V}$	-30	—	—	
Drain-source breakdown voltage (Note 5)	$V_{(BR)DSX}$	$I_D = -10\text{ mA}$, $V_{GS} = 10\text{ V}$	-21	—	—	
Gate threshold voltage	V_{th}	$V_{DS} = -10\text{ V}$, $I_D = -0.1\text{ mA}$	-0.8	—	-2.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -3\text{ A}$	—	29	38	
		$V_{GS} = -10\text{ V}$, $I_D = -3\text{ A}$	—	22	28	$\text{m}\Omega$

Note 5: If a forward bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	—	970	—	pF
Reverse transfer capacitance	C_{rss}		—	170	—	
Output capacitance	C_{oss}		—	200	—	
Switching time (rise time)	t_r	See Fig. 6.2.1	—	7.5	—	ns
Switching time (turn-on time)	t_{on}		—	14	—	
Switching time (fall time)	t_f		—	33	—	
Switching time (turn-off time)	t_{off}		—	116	—	

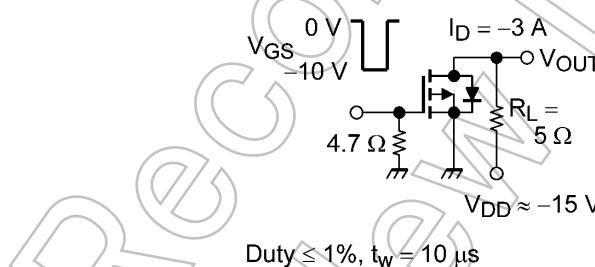


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -24\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -6\text{ A}$	—	22	—	nC
Gate-source charge 1	Q_{gs1}		—	2.4	—	
Gate-drain charge	Q_{gd}		—	5.4	—	

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I_{DRP}	—	—	—	-24	A
Diode forward voltage	V_{DSF}	$I_{DR} = -6\text{ A}$, $V_{GS} = 0\text{ V}$	—	—	1.2	V

Note 6: Ensure that the channel temperature does not exceed 150 °C.

7. Marking

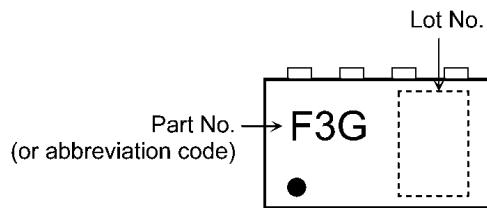
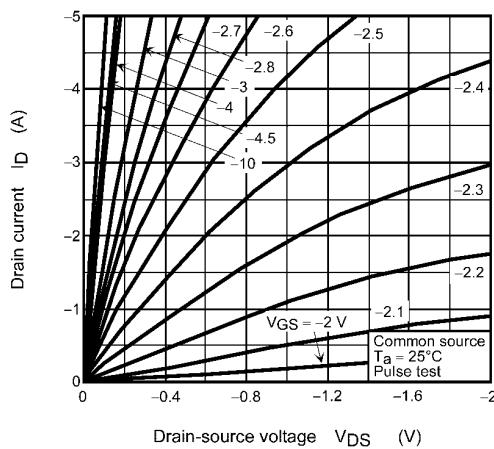
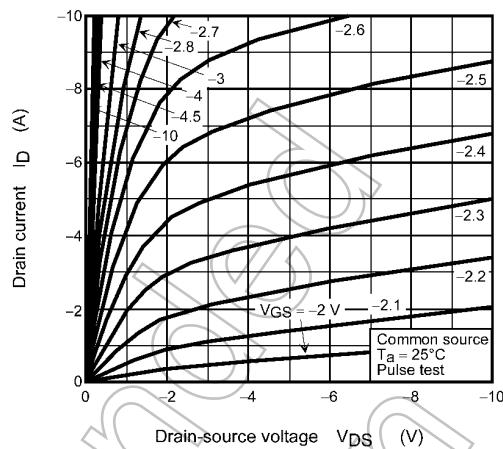
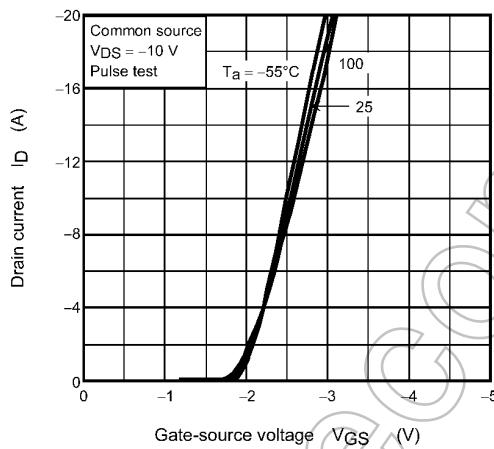
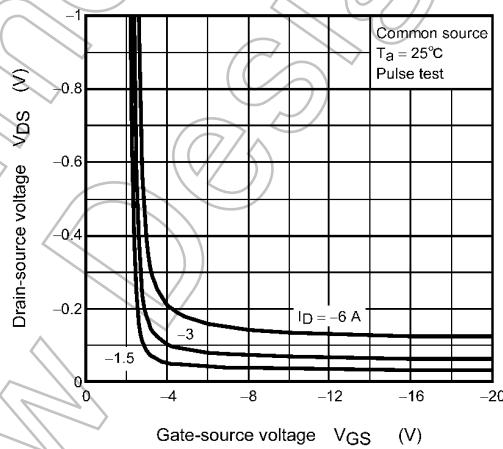
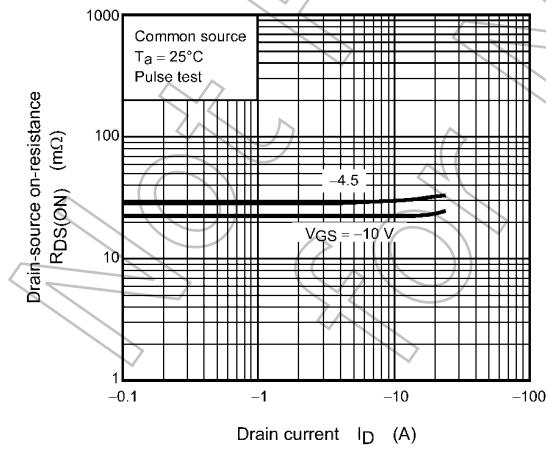
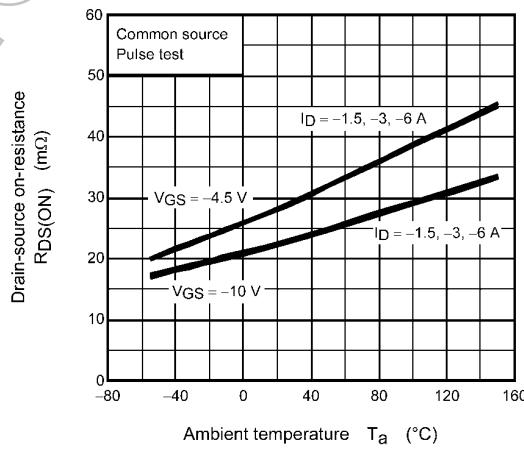


Fig. 7.1 Marking

Not Recommended
for New Design

8. Characteristics Curves (Note)

Fig. 8.1 I_D - V_{DS} Fig. 8.2 I_D - V_{DS} Fig. 8.3 I_D - V_{GS} Fig. 8.4 V_{DS} - V_{GS} Fig. 8.5 $R_{DS(ON)}$ - I_D Fig. 8.6 $R_{DS(ON)}$ - T_a

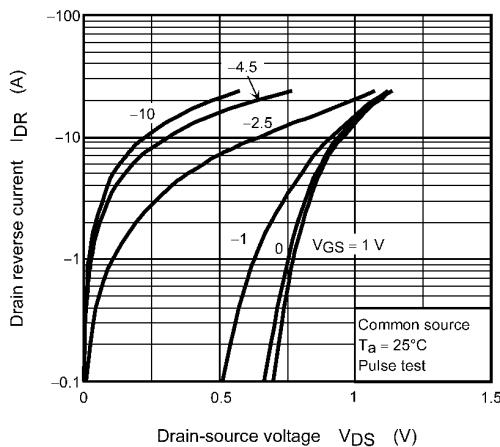
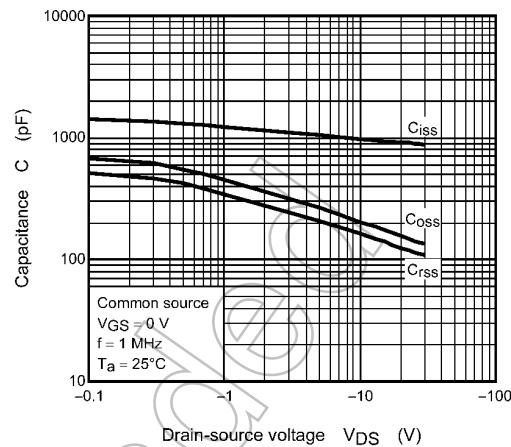
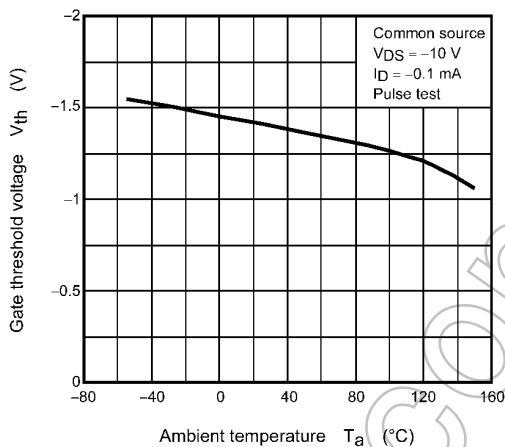
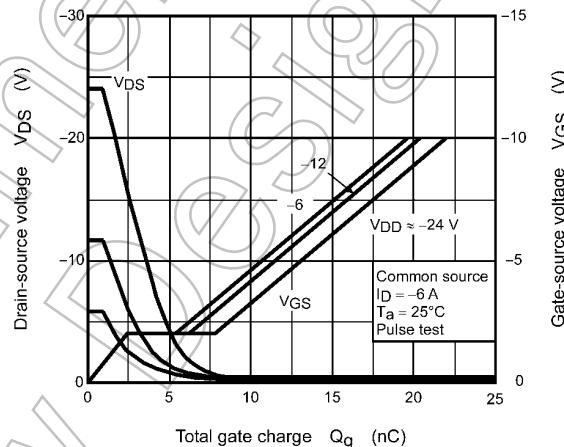
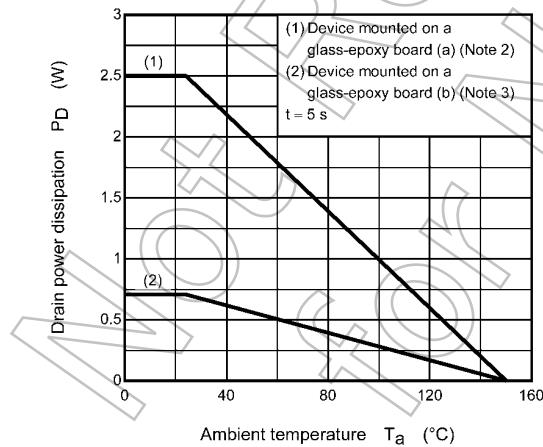
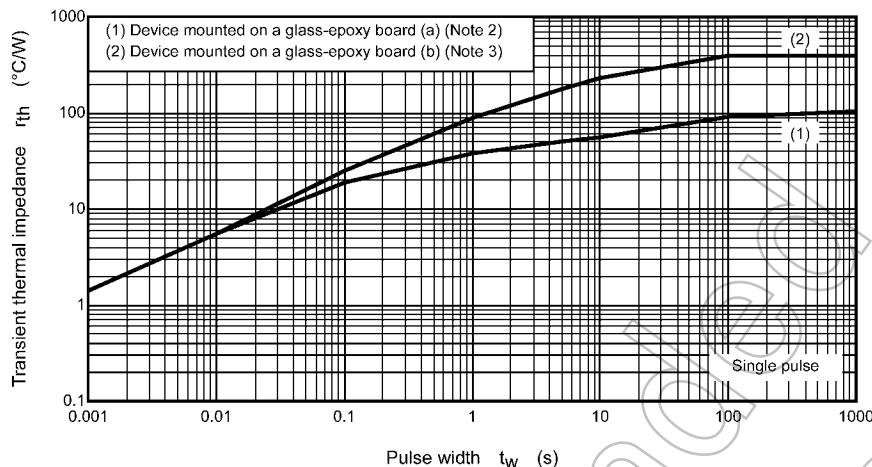
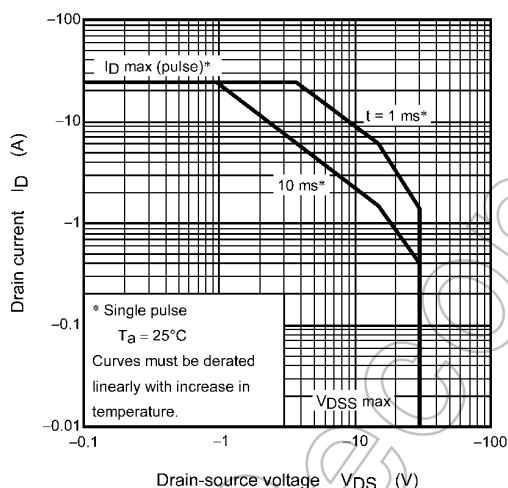
Fig. 8.7 $|IDR|$ - V_{DS} Fig. 8.8 Capacitance - V_{DS} Fig. 8.9 V_{th} - T_a 

Fig. 8.10 Dynamic Input/Output Characteristics

Fig. 8.11 PD - T_a
(Guaranteed Maximum)



**Fig. 8.12 r_{th} - t_w
(Guaranteed Maximum)**

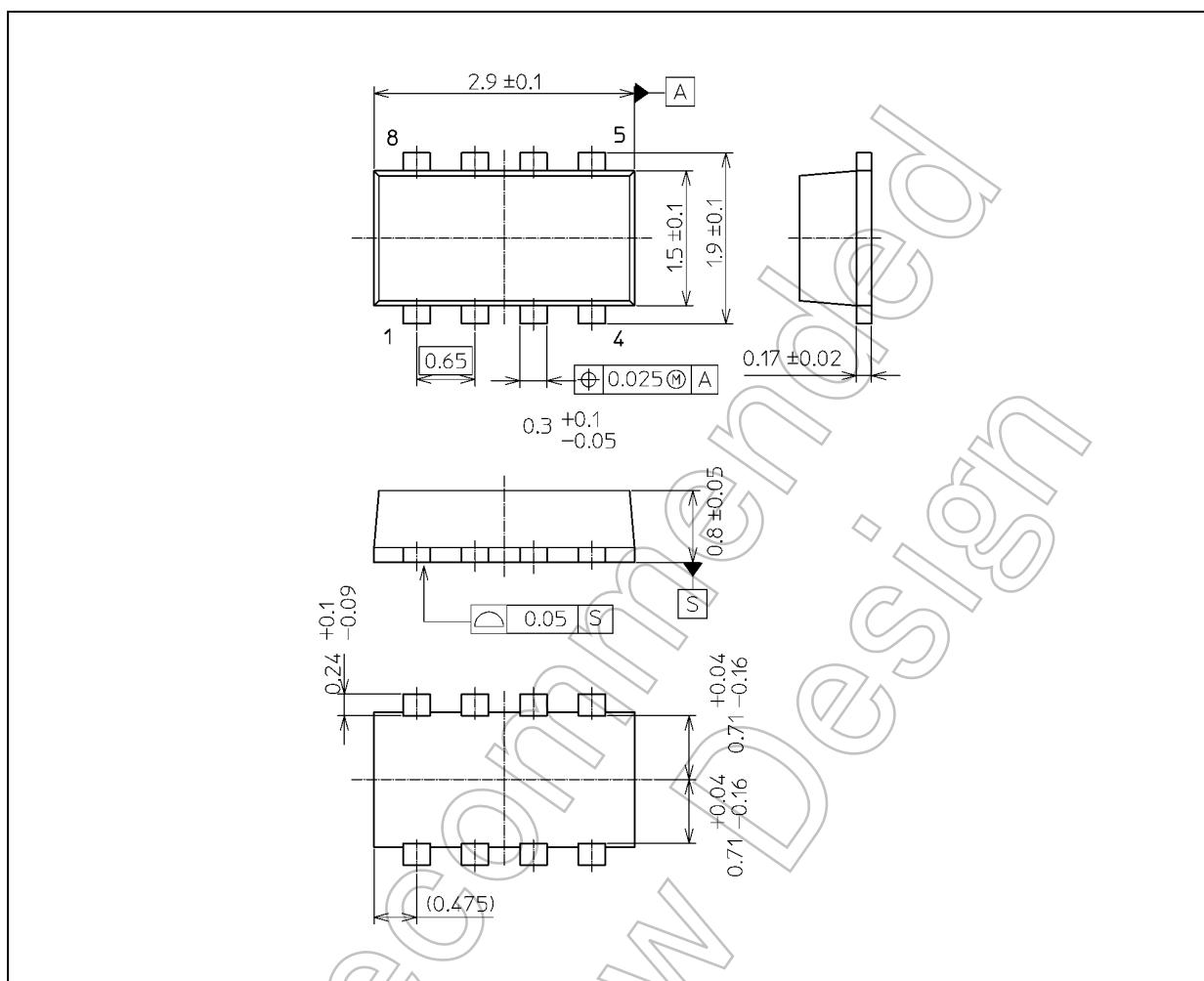


**Fig. 8.13 Safe Operating Area
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)
TOSHIBA: 2-3U1S
Nickname: VS-8

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